深圳市国芯佳品半导体有限公司
SHENZHEN GUOXIN JIAPIN SEMICONDUCTOR CO.LTD

GX3414

20V N-Channel MOSFET

General Description

The GX3414 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 1.8V. This device is suitable for use as a load switch or in PWM applications.

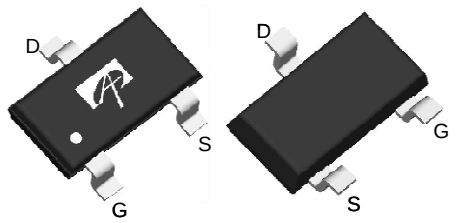
Features

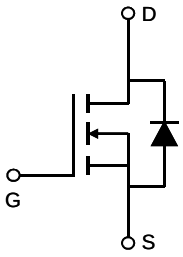
V_{DS} = 20V
I_D = 3A (V_{GS} = 4.5V)
$R_{DS(ON)}$ < 62mΩ (V_{GS} = 4.5V)
$R_{DS(ON)}$ < 70mΩ (V_{GS} = 2.5V)
$R_{DS(ON)}$ < 85mΩ (V_{GS} = 1.8V)

Green Product

SOT23

Top View **Bottom View**





Absolute Maximum Ratings T_A=25℃ unless otherwise noted

Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	20	V
Gate-Source Voltage		V_{GS}	±8	V
Continuous Drain Current [A]	T_A=25℃	I_D	3	A
	T_A=70℃		2.5	
Pulsed Drain Current [B]		I_{DM}	16	
Power Dissipation [A]	T_A=25℃	P_D	1.4	W
	T_A=70℃		0.9	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	℃

Thermal Characteristics

Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient [A]	t ≤ 10s	$R_{\theta JA}$	70	90	℃/W
Maximum Junction-to-Ambient [A]	Steady-State		100	125	℃/W
Maximum Junction-to-Lead [C]	Steady-State	$R_{\theta JL}$	63	80	℃/W

Electrical Characteristics (T_J=25℃ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=250μA, V_{GS}=0V	20			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=20V, V_{GS}=0V			1	μA
		T_J=55℃			5	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}=±8V			100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS} I_D=250μA	0.4	0.7	1	V
$I_{D(ON)}$	On state drain current	V_{GS}=4.5V, V_{DS}=5V	16			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=4.5V, I_D=3A		51	62	mΩ
		T_J=125℃		68	85	
		V_{GS}=2.5V, I_D=2.8A		58	70	mΩ
		V_{GS}=1.8V, I_D=2.5A		68	85	mΩ
g_{FS}	Forward Transconductance	V_{DS}=5V, I_D=3A		11		S
V_{SD}	Diode Forward Voltage	I_S=1A,V_{GS}=0V		0.7	1	V
I_S	Maximum Body-Diode Continuous Current				2	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=10V, f=1MHz		260	320	pF
C_{oss}	Output Capacitance			48		pF
C_{rss}	Reverse Transfer Capacitance			27		pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz		3	4.5	Ω
SWITCHING PARAMETERS						
Q_g	Total Gate Charge	V_{GS}=4.5V, V_{DS}=10V, I_D=3A		2.9	3.8	nC
Q_{gs}	Gate Source Charge			0.4		nC
Q_{gd}	Gate Drain Charge			0.6		nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=5V, V_{DS}=10V, R_L=3.3Ω, R_{GEN}=6Ω		2.5		ns
t_r	Turn-On Rise Time			3.2		ns
$t_{D(off)}$	Turn-Off DelayTime			21		ns
t_f	Turn-Off Fall Time			3		ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=3A, dI/dt=100A/μs		14	19	ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=3A, dI/dt=100A/μs		3.8		nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1 in^2 FR-4 board with 2oz. copper, in a still air environment with T_A=25° C. The value in any given application depends on the user's specific board design. The current rating is based on the t ≤10s thermal resistance rating.
B: Repetitive rating, pulse width limited by junction temperature.
C. The $R_{\theta JA}$ is the sum of the thermal impedence from junction to lead $R_{\theta JL}$ and lead to ambient.
D. The static characteristics in Figures 1 to 6 are obtained using <300 μs pulses, duty cycle 0.5% max.
E. These tests are performed with the device mounted on 1 in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C. The SOA curve provides a single pulse rating.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

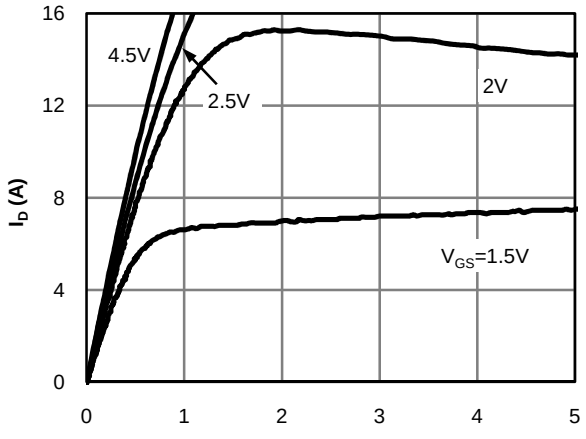


Figure 1: On-Region Characteristics

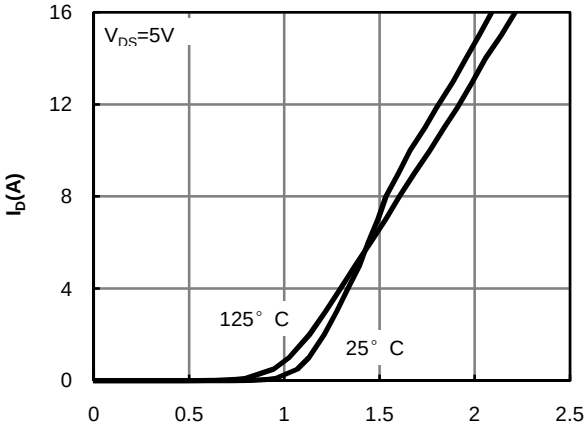


Figure 2: Transfer Characteristics

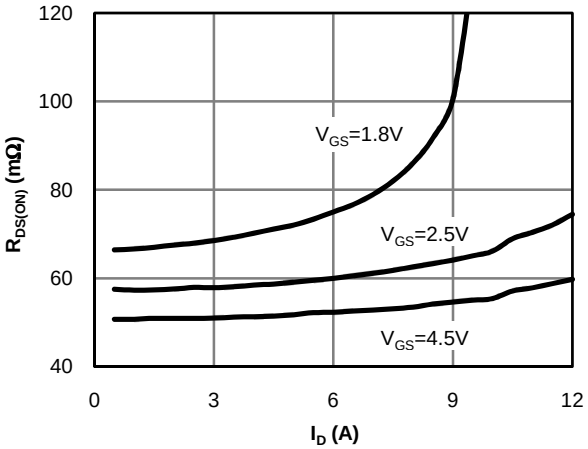


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

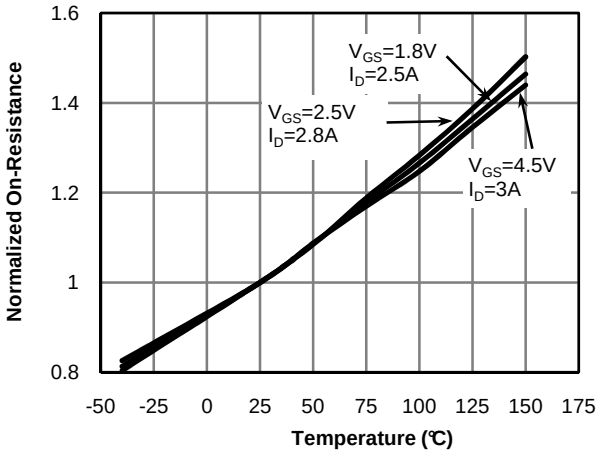


Figure 4: On-Resistance vs. Junction Temperature

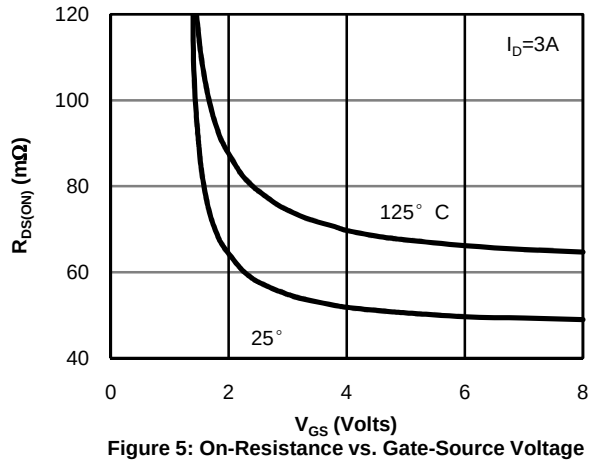


Figure 5: On-Resistance vs. Gate-Source Voltage

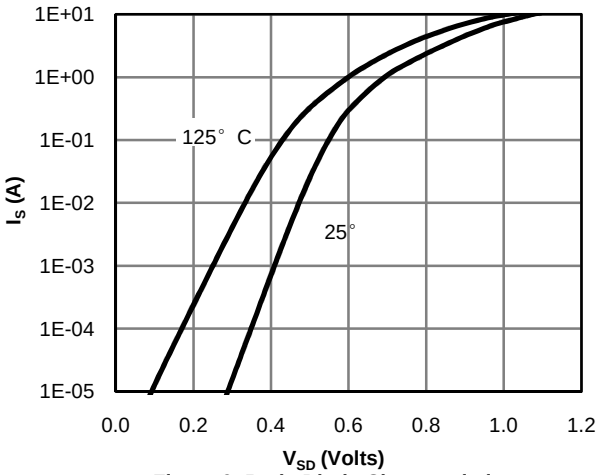


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

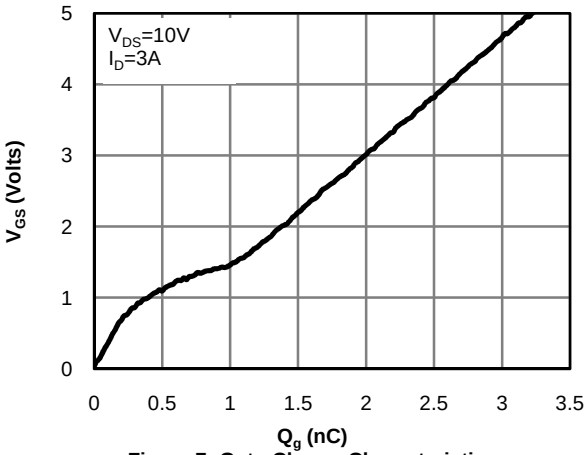


Figure 7: Gate-Charge Characteristics

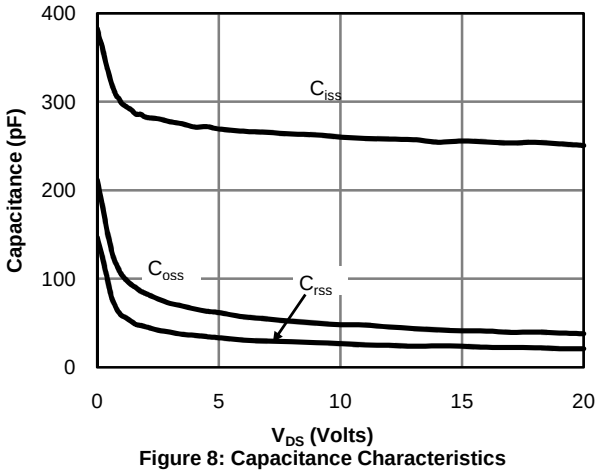


Figure 8: Capacitance Characteristics

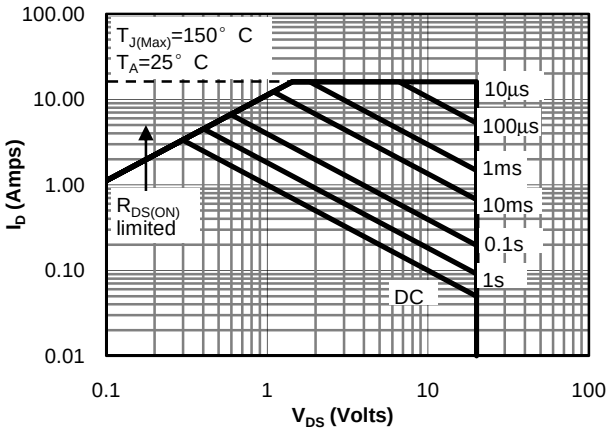


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

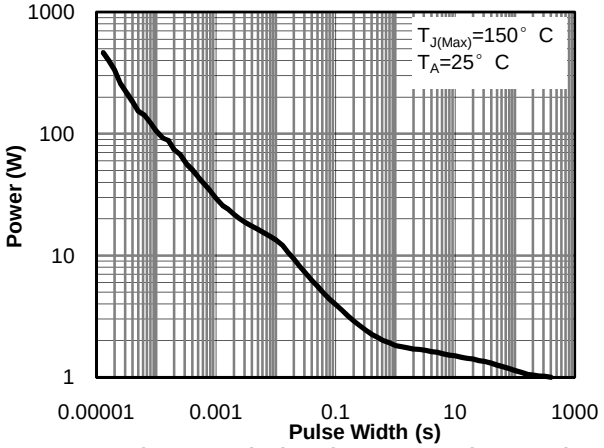


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

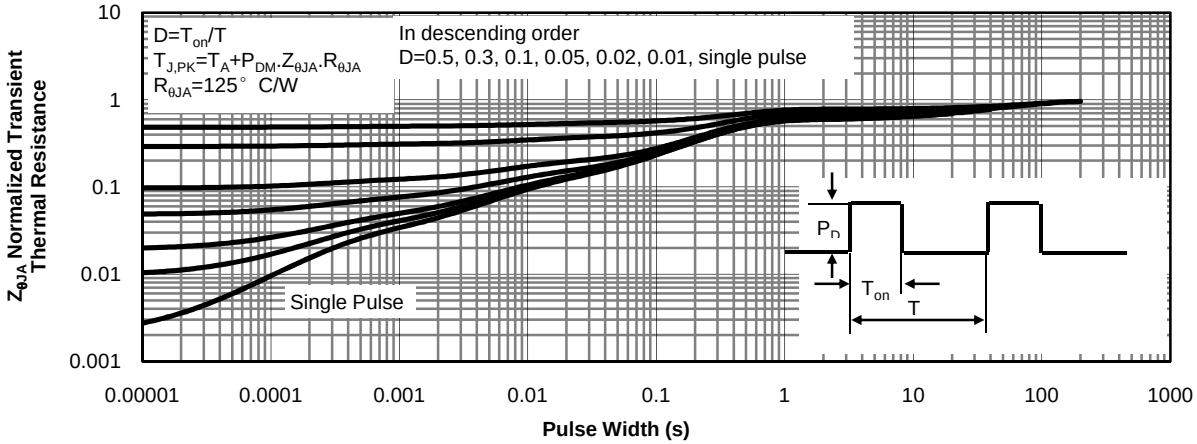
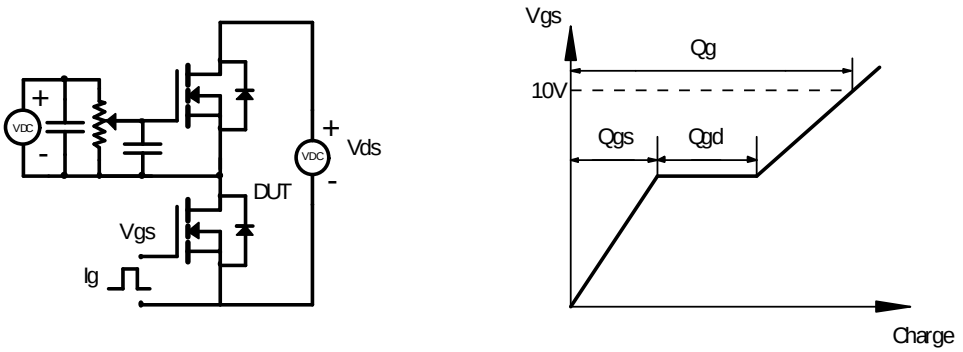
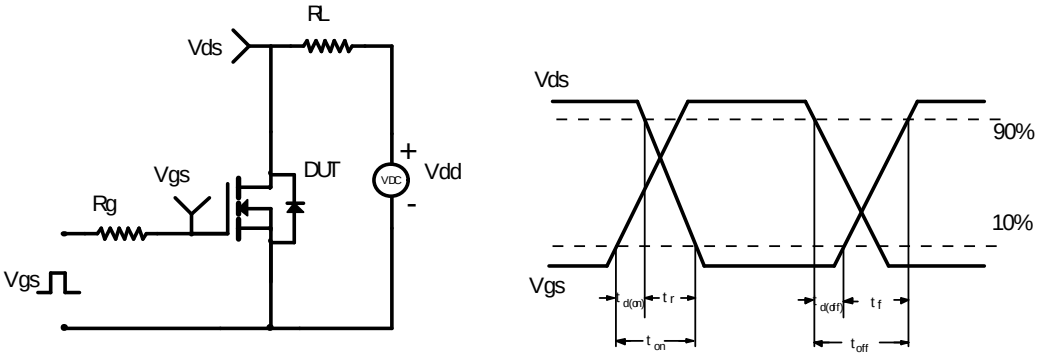


Figure 11: Normalized Maximum Transient Thermal Impedance (Note E)

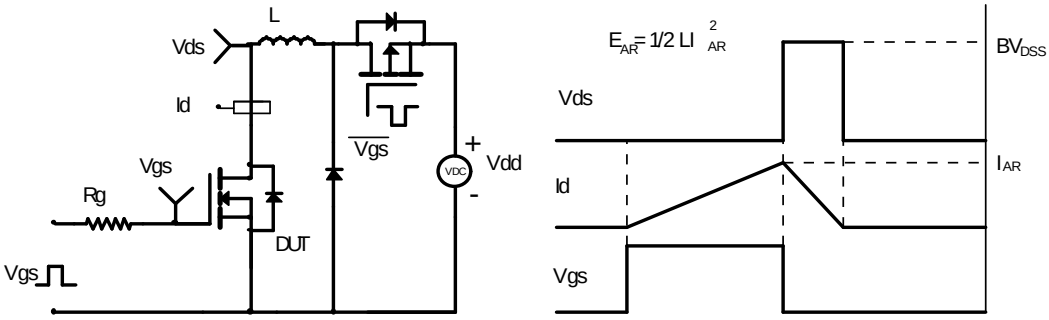
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms